

# HYDROGEN BRIDGING IN THE COMPOUNDS $X_2H$ ( $X = Al, Si, P, S$ )

by

ZACHARY THOMAS OWENS

(Under the Direction of Henry F. Schaefer III)

## ABSTRACT

$X_2H$  hydrides ( $X=Al, Si, P,$  and  $S$ ) have been investigated using coupled cluster theory with single, double, and triple excitations, the latter incorporated as a perturbative correction [CCSD(T)]. These were performed utilizing a series of correlation-consistent basis sets augmented with diffuse functions (aug-cc-pVXZ,  $X = D, T, Q$ ).  $Al_2H$  and  $Si_2H$  are determined to have H-bridged  $C_{2v}$  structures in their ground states: the  $Al_2H$  ground state is of  $^2B_1$  symmetry with an Al-H-Al angle of  $87.6^\circ$ , and the  $Si_2H$  ground state is of  $^2A_1$  symmetry with a Si-H-Si angle of  $79.8^\circ$ . However,  $P_2H$  and  $S_2H$  have non-bridged, bent  $C_s$  structures: the  $P_2H$  ground state is of  $^2A'$  symmetry with a P-P-H angle of  $97.0^\circ$ , and the  $S_2H$  ground state is of  $^2A''$  symmetry with an S-S-H angle of  $93.2^\circ$ . Ground state geometries, vibrational frequencies, and electron affinities have been computed at all levels of theory.

INDEX WORDS: computational chemistry, coupled cluster, hydrogen bridging, quantum chemistry,  $Al_2H$ ,  $Si_2H$ ,  $P_2H$ ,  $S_2H$ , electron affinities

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ZACHARY THOMAS OWENS

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ZACHARY THOMAS OWENS

Major Professor: Henry F. Schaefer III

Committee: Nigel A. Adams  
Geoffrey D. Smith

Electronic Version Approved:

Maureen Grasso  
Dean of the Graduate School  
The University of Georgia  
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## TABLE OF CONTENTS

|  | Page |
|--|------|
| LIST OF TABLES .....   | v    |
| LIST OF FIGURES .....  | vi   |
| CHAPTER  |      |
| 1 INTRODUCTION AND LITERATURE REVIEW .....                               | 1    |
| 2 HYDROGEN BRIDGING IN THE COMPOUNDS $X_2H$ ( $X = Al, Si, P, S$ ) ..... | 4    |
| 2.1 ABSTRACT .....   | 5    |
| 2.2 INTRODUCTION .....   | 6    |
| 2.3 THEORETICAL METHODS .....  | 8    |
| 2.4 RESULTS .....  | 10   |
| 2.5 DISCUSSION .....   | 14   |
| 2.6 CONCLUSIONS .....  | 16   |
| 2.7 ACKNOWLEDGEMENTS .....   | 16   |
| 3 CONCLUDING REMARKS .....   | 27   |
| REFERENCES .....   | 28   |

## LIST OF TABLES

|   | Page |
|---|------|
| TABLE 1: Relative energies (kcal/mol) and harmonic vibrational frequencies ( $\text{cm}^{-1}$ ) for<br>optimized geometries of $\text{Al}_2\text{H}$ and $\text{Si}_2\text{H}$ .....                                      | 17   |
| TABLE 2: Relative energies (kcal/mol) and harmonic vibrational frequencies ( $\text{cm}^{-1}$ ) for<br>the optimized geometries of $\text{P}_2\text{H}$ and $\text{S}_2\text{H}$ .....                                    | 18   |
| TABLE 3: Harmonic vibrational frequencies ( $\text{cm}^{-1}$ ) for the optimized geometries of the<br>$\text{Al}_2\text{H}^-$ , $\text{Si}_2\text{H}^-$ , $\text{P}_2\text{H}^-$ , and $\text{S}_2\text{H}^-$ anions..... | 19   |
| TABLE 4: Adiabatic electron affinities (AEA) for $\text{Al}_2\text{H}$ , $\text{Si}_2\text{H}$ , $\text{P}_2\text{H}$ , and $\text{S}_2\text{H}$ in eV..  | 20   |
| TABLE 5: Dissociation energies of $\text{X}_2\text{H} \rightarrow \text{X}_2 + \text{H}$ ( $\text{X} = \text{Al}, \text{Si}, \text{P}, \text{S}$ ) in kcal/mol.....   | 21   |

## LIST OF FIGURES

|  | Page |
|--|------|
| FIGURE 1: Geometrical parameters of the ${}^2B_1$ $Al_2H$ ground state and the ${}^1A_1$ $Al_2H^-$ anion<br>ground state. ....           | 22   |
| FIGURE 2: Geometrical parameters of the ${}^2A_1$ $Si_2H$ ground state and the ${}^1A_1$ $Si_2H^-$ anion<br>ground state geometries..... | 23   |
| FIGURE 3: Geometrical parameters of the ${}^2A'$ $P_2H$ ground state and the ${}^1A'$ $P_2H^-$ anion<br>ground state .....               | 24   |
| FIGURE 4: Geometrical parameters of the ${}^2A''$ $S_2H$ ground state and the ${}^1A'$ $S_2H^-$ anion<br>ground state. ....              | 25   |
| FIGURE 5: $Si_2H$ ${}^2A_1$ HOMO and $P_2H$ ${}^2A'$ HOMO.....   | 26   |

## CHAPTER 1

### INTRODUCTION AND LITERATURE REVIEW

Before the development of quantum mechanics, chemistry was largely an empirical science, where elements and compounds were categorized into groups and empirical rules about their properties determined. The underlying physical basis for these properties was unknown. Quantum mechanics changed that – most molecular behavior can now be understood from one concept, the solution to the Schrodinger equation.

Dirac once suggested that quantum mechanics changes chemistry into an exercise in applied mathematics. This is true in principle; however, in practice the exact solution to the Schrodinger equation is too difficult to compute for anything but the most trivial chemical systems. Much work has been done on the development of accurate and efficient approximations to the exact solution.

The first approximation made is the Born-Oppenheimer approximation. Since the nuclei in an atom are much heavier than the electrons, they move much more slowly. This allows us to assume that the electrons are moving in a fixed nuclear field, and the kinetic energy of the nuclei can be neglected. The repulsion between the nuclei is considered to be constant. The Born-Oppenheimer approximation lets us solve the electronic Schrodinger equation without worrying about the nuclei.

The electronic Schrodinger equation is still computationally difficult to solve exactly, so a further approximation is made. In Hartree-Fock theory, the wavefunction is represented by a single determinant. Hartree-Fock recovers up to 99% of the total electronic energy of molecules. Unfortunately, that last bit is the part that determines a lot of the chemically



interesting properties. *Ab initio* quantum chemistry methods are a series of corrections to the energy obtained in the Hartree-Fock approximation.

Inclusion of all possible determinants gives the Full Configuration Interaction (FCI) wavefunction. This is the exact non-relativistic energy within the Born Oppenheimer approximation. FCI can be practically computed only for very small systems. Between the HF and FCI extremes are a wide variety of different methods which utilize some subset of the determinants present in FCI. The 3 main families of methods are configuration interaction (CI), perturbation theory, and coupled cluster (CC) theory. Of these, the most accurate, robust, and efficient theory currently is coupled cluster. Like all *ab initio* methods, coupled cluster can currently only be applied to relatively small systems, but as computer power continues to increase, larger and larger systems can be treated with increasing accuracy.

There is another approach to solving the electronic Schrodinger equation that does not depend on explicitly computing the wavefunction like Hartree-Fock and all its refinements do. Density Functional Theory (DFT) is based on the fact that if the exact electron density is known, all the molecular properties can be derived from it. The problem with DFT is that the form of the exact functional is not known. Instead, approximate, parameterized functionals are used, which makes DFT only a semi-empirical method. The advantage of DFT is that its computations are very fast compared to *ab initio* methods, and for a wide variety of systems and properties it gives comparable results.

In the current work, coupled cluster theory including single and double excitations (CCSD) and coupled cluster including single and double excitations plus a perturbative triples contribution [CCSD(T)] are used to determine the properties of several molecules. DFT

calculations are also done on these molecules in order to further determine its accuracy compared to coupled cluster methods.

## CHAPTER 2

HYDROGEN BRIDGING IN THE COMPOUNDS  $X_2H$  ( $X = AL, SI, P, S$ )<sup>†</sup>

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## 2.1 ABSTRACT

$X_2H$  hydrides ( $X=Al$ ,  $Si$ ,  $P$ , and  $S$ ) have been investigated using coupled cluster theory with single, double, and triple excitations, the latter incorporated as a perturbative correction [CCSD(T)]. These were performed utilizing a series of correlation-consistent basis sets augmented with diffuse functions (aug-cc-pVXZ,  $X = D, T, Q$ ).  $Al_2H$  and  $Si_2H$  are determined to have H-bridged  $C_{2v}$  structures in their ground states: the  $Al_2H$  ground state is of  $^2B_1$  symmetry with an Al-H-Al angle of  $87.6^\circ$ , and the  $Si_2H$  ground state is of  $^2A_1$  symmetry with a Si-H-Si angle of  $79.8^\circ$ . However,  $P_2H$  and  $S_2H$  have non-bridged, bent  $C_s$  structures: the  $P_2H$  ground state is of  $^2A'$  symmetry with a P-P-H angle of  $97.0^\circ$ , and the  $S_2H$  ground state is of  $^2A''$  symmetry with an S-S-H angle of  $93.2^\circ$ . Ground state geometries, vibrational frequencies, and electron affinities have been computed at all levels of theory. Our CCSD(T)/aug-cc-pVQZ adiabatic electron affinity of 2.34 eV for the  $Si_2H$  radical is in excellent agreement with the photoelectron spectroscopy experiments of Xu, Taylor, Burton, and Neumark, where the electron affinity was determined to be  $2.31 \pm 0.01$  eV.

## 2.2 INTRODUCTION

Silicon hydrides are relatively abundant species in Chemical Vapor Deposition (CVD) processes, primarily used in the semiconductor industry to produce thin silicon films.<sup>1</sup> In the high temperature plasmas created by this technique, silane ( $\text{SiH}_4$ ) can be transformed<sup>2</sup> into isomers that include, among others, the disilaethynyl radical ( $\text{Si}_2\text{H}$ ) and the disilaethynyl anion ( $\text{Si}_2\text{H}^-$ ). The chemical properties of  $\text{Si}_2\text{H}$  predicted at reliable levels of theory should provide valuable insight into CVD experiments by identifying species that can prevent uniform layer deposition through the scavenging of reactant molecules.

Previously, theory has been used in the case of the valence isoelectronic species  $\text{C}_2\text{H}$ , which is known to have linear equilibrium geometries in its ground and first excited electronic states,<sup>3</sup> and  $\text{Si}_2\text{H}$ , which has been theoretically predicted to have a nonlinear,  $\text{C}_{2v}$  structure in its ground state.<sup>4</sup> It has been shown<sup>5,6</sup> that the difference in chemical properties of carbon and silicon compounds is due to the *s*- and *p*-like valence atomic orbitals of first row atoms being localized in roughly the same region of space, whereas for second and higher row, main group atoms the *s*- and *p*-like atomic orbitals are much more spatially separated. This causes single bonds between first-row elements to be weak and multiple bonds to be strong, while the opposite may be true for second and higher row elements.

While the above has been known for quite some time,<sup>5,6</sup> it provides impetus for understanding the electronic structure of second row hydrides, where the hydrogen bridge-bound  $\text{C}_{2v}$  geometries of the ground electronic states of  $\text{Al}_2\text{H}$  and  $\text{Si}_2\text{H}$  differ from the  $\text{C}_s$  symmetry structure of the  $\text{P}_2\text{H}$  and  $\text{S}_2\text{H}$  hydrides. The properties that are responsible for the unique bonding of these simple hydrides may help describe the more complex bonding environments of

much larger clusters that have been the focus of considerable attention recently.<sup>7-11</sup> For example, binary clusters of silicon and hydrogen are thought to be present in hydrogenated amorphous silicon, porous silicon, and silicon surfaces, and their study may shed light on the complex phenomena occurring in these systems. Since second row clusters may become computationally prohibitive rather quickly as a function of cluster size, insight gained from high level theoretical studies of these smaller species is relevant.

Trans-phosphines,  $XP=PH$ , substituted with electron withdrawing substituents ( $X=F$ ,  $Cl$ ,  $OH$ , and  $NH_2$ ), have been shown to have unusual bridged structures with angles less than  $90^\circ$ . Additionally, trans-phosphine anions and cations can be readily formed via condensation reactions that combine phosphorus ions with phosphines.<sup>12</sup> These  $P_2H^-$  and  $P_2H^+$  species also exhibit a similarly unique, bridged structure and have been investigated extensively with gas-phase ion chemistry techniques.<sup>13</sup> Theoretically, the neutral  $P_2H$  radical has been studied by Fueno and Akagi with MRD-CI methods,<sup>14</sup> predicting that the ground state of the  $P_2H$  radical ( $^2A'$ ) is bent with a P-P-H angle of  $99^\circ$ . Interestingly, the first excited state of  $P_2H$  ( $^2A_2$ ) is a bridged three  $\pi$ -electron system formed by the dehydrogenation of the lowest excited singlet state of  $HP=PH$  ( $^1B$ ).<sup>14</sup>

$S_2H$  was first detected in the flash photolysis of hydrogen sulfide,<sup>15</sup> and then later confirmed in the flash photolysis of hydrogen disulfide.<sup>16</sup> The spectrum was further studied by Gosavi, DeSorgo, Gunning, and Strausz,<sup>17</sup> who reported vibrational spacings of  $\sim 600\text{ cm}^{-1}$ ,  $\sim 900\text{ cm}^{-1}$ , and  $\sim 2500\text{ cm}^{-1}$ , which were assigned to the S-S stretching, S-S-H bending, and S-H stretching modes, respectively. More recently, experiments by Holstein, Fink, Wildt, and Zabel<sup>18</sup> using chemiluminescence from electronically excited  $S_2H$  gave vibrational frequencies of  $904 \pm 8\text{ cm}^{-1}$  for the S-S-H bending mode and  $595 \pm 4\text{ cm}^{-1}$  for the S-S stretching mode. In

1999, Isoniemi, Khriachtchev, Pettersson, and Rasanen<sup>19</sup> isolated H<sub>2</sub>S<sub>2</sub> in an argon matrix and produced S<sub>2</sub>H by photolysis. Their infrared spectra showed S-H stretching modes of 2463 and 2460 cm<sup>-1</sup> at different sites, and an S-S-H bending frequency of 903 cm.<sup>-1</sup> Theoretical studies of S<sub>2</sub>H have also been performed,<sup>20,21</sup> most recently by Zhuo, Cloutier, and Goddard,<sup>22</sup> utilizing UMP2/6-31G(2d) computations that predict geometry and vibrational frequencies consistent with the above experimental results.

In the present study, CCSD(T) methods with a series of correlation consistent basis sets up to the aug-cc-pVQZ level have been used to reliably predict the ground state geometries and vibrational frequencies of the second row hydrides Al<sub>2</sub>H, Si<sub>2</sub>H, P<sub>2</sub>H, and S<sub>2</sub>H. In addition, since the negative ions of P<sub>2</sub>H and Si<sub>2</sub>H are known,<sup>13</sup> and analogous anions of Al<sub>2</sub>H and S<sub>2</sub>H are also suspected, the corresponding ground state anions will also be studied in order to determine the adiabatic electron affinities of these hydrides. Density functional theory computations were also performed to help calibrate our ongoing study of the use of DFT functionals with the DZP++ basis set for predicting electron affinities.<sup>23</sup>

## 2.3 THEORETICAL METHODS

All geometry optimizations and frequency analyses were carried out at the CCSD<sup>24</sup> and CCSD(T)<sup>25,26</sup> level of theory employing the Dunning-Woon<sup>27,28</sup> correlation-consistent polarized valence basis sets augmented with diffuse functions (aug-cc-pVDZ, aug-cc-pVTZ, and aug-cc-pVQZ). The largest basis set, aug-cc-pVQZ was contracted as follows: H(7s4p3d2f/5s4p3d2f), Al(17s12p4d3f2g/7s6p4d3f2g), Si(17s12p4d3f2g/7s6p4d3f2g), P(17s12p4d3f2g/7s6p4d3f2g), S(17s12p4d3f2g/7s6p4d3f2g). In these computations, the ten Hartree-Fock core molecular orbitals (1s-, 2s-, and 2p-like) on aluminum, silicon, phosphorus, and sulfur were frozen.

Computations were also carried out using the HF/DFT hybrid functional designated B3LYP, representing Becke's 3-parameter HF/DFT hybrid exchange functional (B3)<sup>29</sup> coupled with the dynamical correlation functional of Lee, Yang, and Parr (LYP).<sup>30</sup> Double- $\zeta$  quality basis sets with polarization and diffuse functions (DZP++) were used in these geometry optimizations and frequency analyses. The DZP++ basis sets were constructed from the Huzinaga-Dunning-Hay<sup>31,32,33</sup> sets of contracted Gaussian functions. A set of *p*-type polarization functions for each hydrogen atom was added, and one set of five *d*-type polarization functions was included on each heavy atom. These basis sets were further augmented with diffuse functions; a single *s* function for hydrogen, while each heavy atom received one additional *s*-type and one additional set of *p*-type functions. Each of these diffuse orbital exponents was determined in an even tempered sense according to the prescription set forth by Lee and Schaefer,<sup>34</sup>

$$\alpha_{diffuse} = \frac{1}{2} \left( \frac{\alpha_1}{\alpha_2} + \frac{\alpha_2}{\alpha_3} \right) \alpha_1$$

where  $\alpha_1$ ,  $\alpha_2$ , and  $\alpha_3$  are the smallest Gaussian orbital exponents of the *s*- or *p*- type primitive functions for a given atom ( $\alpha_1 < \alpha_2 < \alpha_3$ ) [ $\alpha_s(\text{H}) = 0.04415$ ,  $\alpha_s(\text{Al}) = 0.02148$ ,  $\alpha_p(\text{Al}) = 0.01891$ ,  $\alpha_s(\text{Si}) = 0.02729$ ,  $\alpha_p(\text{Si}) = 0.025$ ,  $\alpha_s(\text{P}) = 0.03448$ ,  $\alpha_p(\text{P}) = 0.03346$ ,  $\alpha_s(\text{S}) = 0.04267$ ,  $\alpha_p(\text{S}) = 0.04096$ ]. The final contraction scheme for the smaller basis sets was as follows: H(5s1p/3s1p), Al(13s9p1d/7s5p1d), Si(13s9p1d/7s5p1d), P(13s9p1d/7s5p1d), S(13s9p1d/7s5p1d).

The forms of the neutral-anion energy difference reported are the adiabatic electron affinity,  $\text{EA}_{\text{ad}} = E(\text{optimized neutral}) - E(\text{optimized anion})$ , the vertical electron affinity,  $\text{VEA} = E(\text{optimized neutral}) - E(\text{anion at neutral geometry})$ , and the vertical detachment energy,  $\text{VDE} = E(\text{neutral at anion geometry}) - E(\text{optimized anion})$ .



DFT computations were carried out using the GAUSSIAN94<sup>35</sup> suite of programs, while the coupled cluster studies were performed with the MOLPRO<sup>36</sup> program package.

## 2.4 RESULTS

Optimized geometries of all species not included here are available in cartesian coordinate format in the supporting information.

### A. $\text{Al}_2\text{H}$

Optimized geometries for the  $\text{Al}_2\text{H}$  radical are shown in Figure 1, where it may be seen that the ground state is predicted to be a hydrogen bridged  $^2\text{B}_1$  structure. There also exists a low lying  $^2\text{A}_1$  minimum predicted to lie only 0.18 kcal/mol higher [aug-cc-pVQZ CCSD(T)] in energy, and it is shown in Table 1S of the supporting information. The  $^2\text{B}_1$  state is a more compact structure than the  $^2\text{A}_1$  minimum, with an Al-Al bond 0.215 Å smaller than the  $^2\text{A}_1$  state. Despite the significant geometry difference, these two states are nearly degenerate in energy at the aug-cc-pVQZ/CCSD(T) level.

B3LYP performs moderately well for predicting the ground state geometry of the  $^2\text{B}_1 \text{ C}_{2v}$  isomer, differing from the CCSD(T) values by a very small 0.004 Å for the Al-H bond distance with a more significant change of 0.036 Å for the Al-Al bond, shown in Figure 1. B3LYP performs similarly for the  $^2\text{A}_1$  isomer. In Table 1, the B3LYP energy separation of the two states is only 1.5 kcal/mol, where the  $^2\text{A}_1$  state is predicted to be the ground state. This differs from the aug-cc-pVQZ/CCSD(T) energy gap by 1.7 kcal/mol and is not surprising considering that the energy separation between the two states is only 0.18 kcal/mol at the highest level of theory. This difference is outside of the expected accuracy range of DFT.<sup>23,37</sup>

The  ${}^1A_1$   $Al_2H^-$  ground state anion, shown in Figure 1, has a somewhat more compact structure than the neutral radical, with the Al-Al bond shortening by 0.050 Å and the Al-Al-H angle increasing by 0.85°, but it remains hydrogen bridged. Adding an electron to the  $Al_2H$  system stabilizes the radical, and the lower energy anion yields an adiabatic electron affinity of 1.11 eV at the aug-cc-pVQZ/CCSD(T) level of theory. The DZP++/B3LYP (0.95 eV), B3LYP (0.85 eV), and BLYP (0.83 eV) electron affinities differ from the CCSD(T) result; however, the BP86 method (1.11 eV) shows excellent agreement, see Table 4.

## B. $Si_2H$

The optimized geometry for the ground state of the  $Si_2H$  radical is shown in Figure 2, and is an H-bridged  ${}^2A_1$  structure, similar to the  $Al_2H$  system. Again, a low lying  ${}^2B_1$  minimum is predicted to lie only 0.33 kcal/mol higher in energy than this ground state, and it is shown in the Supporting Information. In contrast to  $Al_2H$ , these two structures do not have a large geometry difference, with the  ${}^2B_1$  state having an Si-Si bond length only 0.084 Å longer than the  ${}^2A_1$  ground state. These two nearly degenerate states have been studied earlier<sup>4,38-41</sup> with an extensive variety of theoretical methods up to CCSDT, and our work is in good agreement with previous results of Pak *et al.*<sup>4</sup>, who predicted the energy separation to be 0.37 kcal/mol at their most reliable level of theory, cc-pCVQZ CCSD(T). A vibrationally resolved photoelectron spectrum of  $Si_2H^-$  has been obtained by Xu, Taylor, Burton, and Neumark.<sup>42</sup> From their own *ab initio* computations, Neumark and coworkers predicted that photodetachment to the  ${}^2A_1$  state results in a smaller geometry change than to the  ${}^2B_1$  state, and assigned the ground state to be  ${}^2A_1$ . The experimental excitation energy  $T_0({}^2B_1)$  is  $0.020 \pm 0.005$  eV, consistent with our theoretical result of 0.014 eV. We also find a linear  $Si_2H$  minimum – the  ${}^2\Sigma^+$  state shown in

Table 1S of the Supporting Information and this isomer is 45.0 kcal/mol above the  $^2A_1$  ground state. In addition, a linear  $^2\Pi$  transition state, 9.3 kcal/mol above the ground state has been located.

B3LYP performs well in predicting the geometries of the  $C_{2v}$   $Si_2H$  structures, with only small differences in bond lengths and angles (0.006 Å and 0.015 Å for the Si-Si bonds and 0.22° and 0.16° for the Si-Si-H angles), as may be seen in Figure 2 and Table 1S of the Supporting Information. However, the B3LYP DFT functional computes the wrong ground state for this molecule, predicting the  $^2B_1$  state to be 0.97 kcal/mol lower in energy than the true ground state,  $^2A_1$  giving an error of the energy splitting between the two states by 1.30 kcal/mol when compared to aug-cc-pVQZ/CCSD(T).

Adding an electron does not cause a large geometry change, as may be seen in the  $^1A_1$  ground state  $Si_2H^-$  anion structure shown in Figure 2. The Si-Si bond shortens by 0.022 Å and the Si-Si-H angle decreases by 0.52°. Again, the extra electron stabilizes the radical, resulting in a computed adiabatic electron affinity of 2.34 eV at the aug-cc-pVQZ/CCSD(T) level of theory. The experimental electron affinity from Neumark<sup>42</sup> is  $2.31 \pm 0.01$  eV, in excellent agreement with our results. In this case B3LYP also gives good agreement with the experimental electron affinity, with an AEA value of 2.31 eV. The other functionals do not perform as well, predicting the following electron affinities: BLYP 2.12 eV, BP86 2.38 eV, and BHLYP 2.20 eV.

### C. $P_2H$

For the case of  $P_2H$ , we find that a hydrogen-bridged  $C_{2v}$  structure is no longer the ground electronic state. Instead, a bent  $^2A'$  structure is predicted to be the global minimum shown in Figure 3. The lowest energy hydrogen bridged isomer was a  $^2A_2$  state 28.3 kcal/mol

above the bent ground state and is included in the Supporting Information. There also exists a  $^2B_1$  transition state (Supporting Information) 87.1 kcal/mol above the  $^2A'$  ground state. This is a transition state between the two bent structures where the hydrogen atom is transferred from one phosphorus atom to the other. Indeed, animation of the imaginary mode corresponds to this motion, confirming the hydrogen transfer, although no intrinsic reaction coordinate (IRC)<sup>43</sup> computations were performed. B3LYP predicts a similar geometry compared to coupled cluster theory for the  $^2A'$  ground state (Figure 3).

The  $P_2H^-$  anion ( $^1A_1$ ), shown in Figure 3, has a P-P-H bond angle  $8.6^\circ$  larger than that for the neutral radical, with P-P and the P-H bonds lengthening by 0.020 Å and 0.028 Å respectively. The adiabatic electron affinity is predicted to be 1.51 eV at the CCSD(T)/aug-cc-pVQZ level, with the B3LYP/DZP++ EA in very close agreement (1.53 eV) to CCSD(T). The BLYP, BP86, and BHLYP functionals predict adiabatic electron affinities of 1.38, 1.61, and 1.35 eV respectively.

#### D. $S_2H$

Our computations predict  $S_2H$  to have a bent geometry of  $^2A''$  symmetry as the ground state minimum. This structure is shown in Figure 4, similar to  $P_2H$ , but having an X-X-H angle  $4.3^\circ$  larger. A bent  $C_s$  geometry of  $^2A'$  symmetry was also located 19.9 kcal/mol higher in energy (Supporting Information). As may be seen from Figure 4, B3LYP predicts a similar geometry to CCSD(T) differing in S-S bond length by 0.03 Å and in bond angle by 0.9 degrees.

The computed adiabatic electron affinity at the CCSD(T)/aug-cc-pVQZ level is 1.93 eV and, as in the  $P_2H$  case, B3LYP with the DZP++ basis again predicts the AEA to be 0.02 eV larger. As with the above hydrides presented here, the other DFT functionals do not perform as

well as B3LYP. Using BLYP, we obtained an adiabatic electron affinity of 1.77 eV; computations using BP86 result in 1.96 eV; and finally, the BHLYP functional gives an adiabatic electron affinity of 1.84 eV (Table 4). The geometry change in going from the  $S_2H^-$  anion, as shown in Figure 4, is not as large as that for the  $P_2H$  system. The S-S distance is longer in  $S_2H^-$  by 0.13 Å and the S-S-H bond angle is 0.1° larger.

## 2.5 DISCUSSION

The change in geometry from  $Si_2H$  to  $P_2H$  can be attributed to the bonding environment of the two heavy elements. Fueno and Akagi<sup>14</sup> illustrated the molecular orbital diagram for the first excited state of the  $P_2H$  radical and conclude from this that a stabilizing interaction occurs with the maximal overlap of the H-1s orbital and the  $P_2-\pi_u$  orbitals. Drawing our own inference from the molecular orbitals in their schematic, the occupation of the phosphorus dimer  $\pi_u$  orbitals determines whether or not these  $X_2H$  hydrides are hydrogen bridged. Incomplete occupation of the  $\pi_u$  orbitals in the  $Al_2H$  and  $Si_2H$  species maximizes the overlap of the H-1s orbital and the  $P_2-\pi_u$  orbitals favoring the hydrogen bridged structure as seen in the first excited state of the  $P_2H$  radical. This effect is also seen in the  $P_2H^+$  cation and the  $H_2P_2^+$  cation, having been demonstrated by Fueno and Akagi.<sup>14</sup> In the case of  $P_2H$  and  $S_2H$ , the diatomic  $\pi_u$  orbitals are fully occupied, strengthening the P-P and S-S bonds and thus weakening the hydrogen interaction with the two heavy elements. This nonbridged structure causes a weak H-P bond through the occupation of the H-1s orbital to a  $P_2-\pi_g^*$  anti-bonding orbital.

The above effect is illustrated in Figure 5, where the HOMOs of  $Si_2H$  and  $P_2H$  are plotted, showing the favorable bonding interaction in the case of  $Si_2H$  and the antibonding

overlap in  $P_2H$ . Table 5 also demonstrates the strength of the  $H-X_2$  bonds showing a minimum in the hydrogen dissociation energy for  $P_2H$ .

All four molecules have appreciably large and positive electron affinities. The trend across the period in electron affinities is consistent with the change in geometry at the Si-P divide. One sees an increase in EA from  $Al_2H$  to  $Si_2H$  as expected, and then a decrease to  $P_2H$  before rising again in the  $S_2H$  case. The decrease in electron affinity corresponds to the occupation of the  $\pi_g^*$  antibonding orbitals in the phosphorous and sulfur hydrides, destabilizing the anion.

Density functional theory, in particular the B3LYP functional paired with a DZP++ basis set, has proven to be an inexpensive and effective method of computing electron affinities.<sup>23</sup> For  $P_2H$  and  $S_2H$ , B3LYP predicted adiabatic electron affinities fall only 0.02 eV above the much more computationally demanding aug-cc-pVQZ/CCSD(T) level of theory.  $Al_2H$  and  $Si_2H$  both have a very low-lying excited electronic state, less than 0.5 kcal in energy above the ground state, and in these two cases B3LYP failed to predict the correct ground state for the neutral molecule. The BLYP and BHLYP functionals consistently underestimated the electron affinities compared to CCSD(T) while the BP86 overestimated the EAs in all cases. The magnitude of the errors for these three functionals varied for the different systems.

Only the  $Si_2H$  electron affinity has been determined experimentally, namely to be  $2.31 \pm 0.01$  eV<sup>42</sup>; therefore direct comparisons with experimental data is limited. However, for  $Si_2H$ , the aug-cc-pVQZ/CCSD(T) method predicts an EA of 2.34 eV in very close agreement to the experimental value. As discussed previously, B3LYP determines the wrong ground state for this molecule but, when constrained to the correct electronic state, B3LYP predicted an adiabatic electron affinity of 2.31, a result fortuitously better than CCSD(T).

## 2.6 CONCLUSIONS

From high level structural studies of the  $X_2H$  hydrides ( $X=Al$ ,  $Si$ ,  $P$ , and  $S$ ) we have demonstrated the  $Al_2H$  and  $Si_2H$  species to have H-bridged structures of  $C_{2v}$  symmetry as their ground electronic states while the  $P_2H$  and  $S_2H$  isomers were found to have bent structures of  $C_s$  symmetry. This interesting change in ground state geometry may be attributed to a favorable overlap of the aluminum and silicon  $\pi_u$  bonding orbitals with the hydrogen  $1s$  orbital becoming unfavorable for the phosphorous and sulfur hydrides.

The B3LYP/DZP++ level of theory has again proven to be a rather robust method for computing electron affinities, comparing well to our most rigorous theoretical methods for these  $X_2H$  hydrides. In fact, B3LYP provided results for electron affinities nearly comparable in accuracy to the CCSD(T)/aug-cc-pVQZ method. The AEA at the CCSD(T)/aug-cc-pVQZ (B3LYP/DZP++) levels for  $Al_2H$  are predicted to be 1.11 eV (0.95 eV); for  $Si_2H$  the AEAs are 2.34 eV(2.31 eV); for  $P_2H$  the AEAs are 1.51 eV(1.53 eV); and for  $S_2H$  the AEAs are 1.93 eV(1.95 eV). With the exception of BP86 for  $Al_2H$ , the BLYP, BP86, and BHLYP functionals were not as successful as B3LYP in predicting adiabatic electron affinities.

## 2.7 ACKNOWLEDGEMENTS

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TABLE 1. Relative energies (kcal/mol) and harmonic vibrational frequencies ( $\text{cm}^{-1}$ ) for optimized geometries of  $\text{Al}_2\text{H}$  and  $\text{Si}_2\text{H}$ .

| $\text{Al}_2\text{H}$ | Method                              | Energy | $\omega_1$ | $\omega_2$ | $\omega_3$ | $\omega_3$ |
|-----------------------|-------------------------------------|--------|------------|------------|------------|------------|
| $^2\text{B}_1$        | DZP++ B3LYP                         | 1.5    | 1228       | 1015       | 259        |            |
|                       | aug-cc-pVQZ CCSD                    | 1.6    | 1236       | 1050       | 278        |            |
|                       | aug-cc-pVQZ CCSD(T)                 | 0.0    | 1242       | 1025       | 298        |            |
| $^2\text{A}_1$        | DZP++ B3LYP                         | 0.0    | 1075       | 996        | 218        |            |
|                       | aug-cc-pVQZ CCSD                    | 0.0    | 1092       | 992        | 257        |            |
|                       | aug-cc-pVQZ CCSD(T)                 | 0.2    | 1096       | 988        | 260        |            |
| $\text{Si}_2\text{H}$ | Method                              | Energy | $\omega_1$ | $\omega_2$ | $\omega_3$ | $\omega_3$ |
| $^2\text{A}_1$        | DZP++ B3LYP                         | 1.0    | 1567       | 1090       | 544        |            |
|                       | aug-cc-pVQZ CCSD                    | 2.1    | 1589       | 1166       | 555        |            |
|                       | aug-cc-pVQZ CCSD(T)                 | 0.0    | 1574       | 1157       | 546        |            |
|                       | Experiment [Neumark <sup>42</sup> ] |        | 1592       |            | 540        |            |
| $^2\text{B}_1$        | DZP++ B3LYP                         | 0.0    | 1472       | 1012       | 512        |            |
|                       | aug-cc-pVQZ CCSD                    | 0.0    | 1504       | 1057       | 548        |            |
|                       | aug-cc-pVQZ CCSD(T)                 | 0.3    | 1490       | 1082       | 529        |            |
|                       | Experiment [Neumark <sup>42</sup> ] |        | 1491       |            | 520        |            |
| $^2\Pi$               | DZP++ B3LYP                         | 8.9    | 2183       | 569        | 49         | 40i        |
|                       | aug-cc-pVQZ CCSD                    | 10.4   | 2220       | 592        | 130        | 87i        |
|                       | aug-cc-pVQZ CCSD(T)                 | 9.3    | 2187       | 568        | 82         | 83i        |
| $^2\Sigma^+$          | aug-cc-pVQZ CCSD                    | 48.3   | 2303       | 719        | 446        | 446        |
|                       | aug-cc-pVQZ CCSD(T)                 | 45.0   | 2263       | 683        | 354        | 354        |



TABLE 2. Relative energies (kcal/mol) and harmonic vibrational frequencies ( $\text{cm}^{-1}$ ) for the optimized geometries of  $\text{P}_2\text{H}$  and  $\text{S}_2\text{H}$ .

| $\text{P}_2\text{H}$ | Method                               | Energy | $\omega_1$ | $\omega_2$ | $\omega_3$ | $\omega_3$ |
|----------------------|--------------------------------------|--------|------------|------------|------------|------------|
| $^2\text{A}'$        | DZP++ B3LYP                          | 0.0    | 2264       | 673        | 604        |            |
|                      | aug-cc-pVQZ CCSD                     | 0.0    | 2336       | 682        | 639        |            |
|                      | aug-cc-pVQZ CCSD(T)                  | 0.0    | 2305       | 663        | 610        |            |
| $^2\text{A}_2$       | aug-cc-pVQZ CCSD                     | 28.5   | 1773       | 660        | 1057       |            |
|                      | aug-cc-pVQZ CCSD(T)                  | 28.3   | 1751       | 635        | 1100       |            |
| $^2\Pi$              | aug-cc-pVQZ CCSD                     | 42.9   | 2563       | 711        | 202i       | 1501i      |
|                      | aug-cc-pVQZ CCSD(T)                  | 40.4   | 2522       | 685        | 205i       | 1508i      |
| $^2\text{B}_1$       | aug-cc-pVQZ CCSD                     | 88.6   | 1720       | 470        | 1554i      |            |
|                      | aug-cc-pVQZ CCSD(T)                  | 87.1   | 1674       | 454        | 1591i      |            |
| $\text{S}_2\text{H}$ | Method                               | Energy | $\omega_1$ | $\omega_2$ | $\omega_3$ | $\omega_3$ |
| $^2\text{A}''$       | DZP++ B3LYP                          | 0.0    | 2554       | 910        | 559        |            |
|                      | aug-cc-pVQZ CCSD                     | 0.0    | 2647       | 933        | 603        |            |
|                      | aug-cc-pVQZ CCSD(T)                  | 0.0    | 2608       | 921        | 599        |            |
|                      | Experiment [Isoniemi <sup>19</sup> ] |        | 2463       | 903        |            |            |
|                      | Experiment [Holstein <sup>18</sup> ] |        |            | 904        | 595        |            |
| $^2\text{A}'$        | aug-cc-pVQZ CCSD                     | 18.9   | 2706       | 794        | 517        |            |
|                      | aug-cc-pVQZ CCSD(T)                  | 19.9   | 2674       | 769        | 505        |            |
|                      | Experiment [Holstein <sup>18</sup> ] |        |            |            | 504        |            |
| $^2\Pi$              | DZP++ B3LYP                          | 70.2   | 2748       | 504        | 1395i      | 1718i      |
|                      | aug-cc-pVQZ CCSD                     | 73.4   | 2797       | 582        | 1458i      | 1810i      |
|                      | aug-cc-pVQZ CCSD(T)                  | 71.1   | 2758       | 566        | 1425i      | 1789i      |

TABLE 3. Harmonic vibrational frequencies ( $\text{cm}^{-1}$ ) for the optimized geometries of the  $\text{Al}_2\text{H}^-$ ,  $\text{Si}_2\text{H}^-$ ,  $\text{P}_2\text{H}^-$ , and  $\text{S}_2\text{H}^-$  anions.

| Method                  |                     | $\omega_1$ | $\omega_2$ | $\omega_3$ |
|-------------------------|---------------------|------------|------------|------------|
| $\text{Al}_2\text{H}^-$ | DZP++ B3LYP         | 1213       | 1028       | 292        |
|                         | aug-cc-pVQZ CCSD    | 1225       | 1077       | 311        |
|                         | aug-cc-pVQZ CCSD(T) | 1223       | 1042       | 325        |
| $\text{Si}_2\text{H}^-$ | DZP++ B3LYP         | 1487       | 1081       | 557        |
|                         | aug-cc-pVQZ CCSD    | 1521       | 1147       | 582        |
|                         | aug-cc-pVQZ CCSD(T) | 1508       | 1172       | 558        |
| $\text{P}_2\text{H}^-$  | DZP++ B3LYP         | 1988       | 824        | 587        |
|                         | aug-cc-pVQZ CCSD    | 2097       | 831        | 619        |
|                         | aug-cc-pVQZ CCSD(T) | 2050       | 812        | 597        |
| $\text{S}_2\text{H}^-$  | DZP++ B3LYP         | 2542       | 808        | 415        |
|                         | aug-cc-pVQZ CCSD    | 2638       | 839        | 488        |
|                         | aug-cc-pVQZ CCSD(T) | 2599       | 822        | 478        |

TABLE 4. Adiabatic electron affinities (AEA) for Al<sub>2</sub>H, Si<sub>2</sub>H, P<sub>2</sub>H, and S<sub>2</sub>H in eV.

|  | AEA (eV) | VEA (eV) | VDE (eV) |
|--|----------|----------|----------|
| <sup>2</sup> B <sub>1</sub> → <sup>1</sup> A <sub>1</sub> Transition |          |          |          |
| Al <sub>2</sub> H DZP++ B3LYP  | 0.95     | 0.94     | 0.96     |
| Al <sub>2</sub> H DZP++ BLYP   | 0.83     | 0.82     | 0.84     |
| Al <sub>2</sub> H DZP++ BP86   | 1.11     | 1.10     | 1.12     |
| Al <sub>2</sub> H DZP++ BHLYP  | 0.85     | 0.75     | 0.88     |
| Al <sub>2</sub> H aug-cc-pVQZ CCSD                                   | 0.96     | 0.95     | 0.97     |
| Al <sub>2</sub> H aug-cc-pVQZ CCSD(T)                                | 1.11     | 1.10     | 1.38     |
| <sup>2</sup> A <sub>1</sub> → <sup>1</sup> A <sub>1</sub> Transition |          |          |          |
| Si <sub>2</sub> H DZP++ B3LYP  | 2.31     | 2.30     | 2.31     |
| Si <sub>2</sub> H DZP++ BLYP   | 2.12     | 2.12     | 2.13     |
| Si <sub>2</sub> H DZP++ BP86   | 2.38     | 2.37     | 2.39     |
| Si <sub>2</sub> H DZP++ BHLYP  | 2.20     | 2.20     | 2.20     |
| Si <sub>2</sub> H aug-cc-pVQZ CCSD                                   | 2.28     | 2.28     | 2.29     |
| Si <sub>2</sub> H aug-cc-pVQZ CCSD(T)                                | 2.34     | 2.34     | 2.34     |
| Experiment [Neumark <sup>41</sup> ]                                  | 2.31     |          |          |
| <sup>2</sup> A' → <sup>1</sup> A' Transition                         |          |          |          |
| P <sub>2</sub> H DZP++ B3LYP   | 1.53     | 1.46     | 1.58     |
| P <sub>2</sub> H DZP++ BLYP  | 1.38     | 1.32     | 1.44     |
| P <sub>2</sub> H DZP++ BP86  | 1.61     | 1.54     | 1.66     |
| P <sub>2</sub> H DZP++ BHLYP   | 1.35     | 1.29     | 1.40     |
| P <sub>2</sub> H aug-cc-pVQZ CCSD                                    | 1.43     | 1.37     | 1.48     |
| P <sub>2</sub> H aug-cc-pVQZ CCSD(T)                                 | 1.51     | 1.44     | 1.56     |
| <sup>2</sup> A'' → <sup>1</sup> A' Transition                        |          |          |          |
| S <sub>2</sub> H DZP++ B3LYP   | 1.95     | 1.81     | 2.11     |
| S <sub>2</sub> H DZP++ BLYP  | 1.77     | 1.63     | 1.92     |
| S <sub>2</sub> H DZP++ BP86  | 1.96     | 1.83     | 2.10     |
| S <sub>2</sub> H DZP++ BHLYP   | 1.84     | 1.69     | 1.99     |
| S <sub>2</sub> H aug-cc-pVQZ CCSD                                    | 1.88     | 1.74     | 2.73     |
| S <sub>2</sub> H aug-cc-pVQZ CCSD(T)                                 | 1.93     | 1.79     | 2.83     |

TABLE 5. Dissociation energies of  $X_2H \rightarrow X_2 + H$  ( $X = Al, Si, P, S$ ) in kcal/mol.

| Dissociation Energy         |      |
|-----------------------------|------|
| $Al_2H$ aug-cc-pVQZ CCSD(T) | 81.5 |
| $Si_2H$ aug-cc-pVQZ CCSD(T) | 88.2 |
| $P_2H$ aug-cc-pVQZ CCSD(T)  | 36.9 |
| $S_2H$ aug-cc-pVQZ CCSD(T)  | 77.4 |

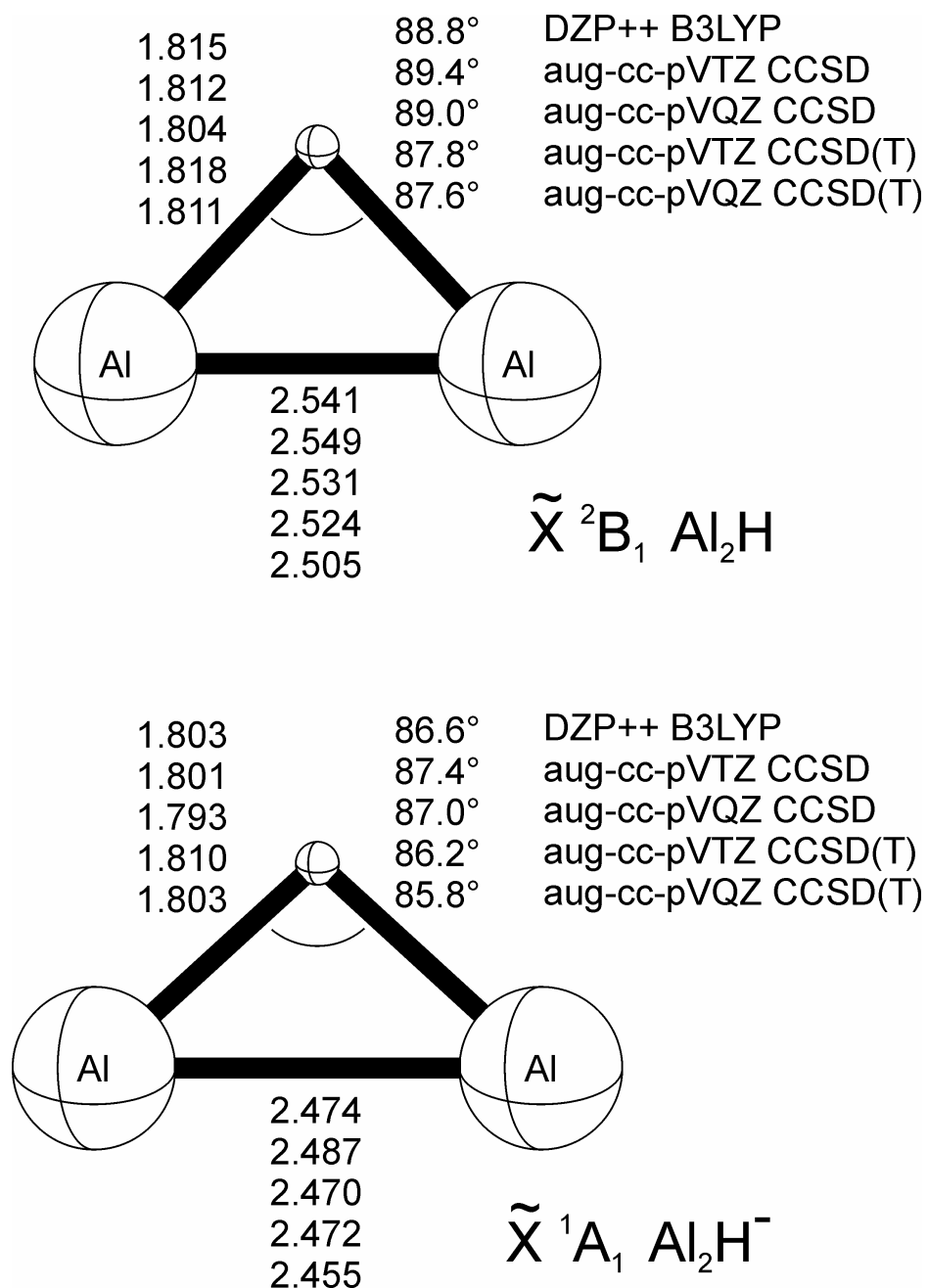


FIGURE 1. Geometrical parameters of the  $^2B_1$   $Al_2H$  ground state and the  $^1A_1$   $Al_2H^-$  anion ground state.

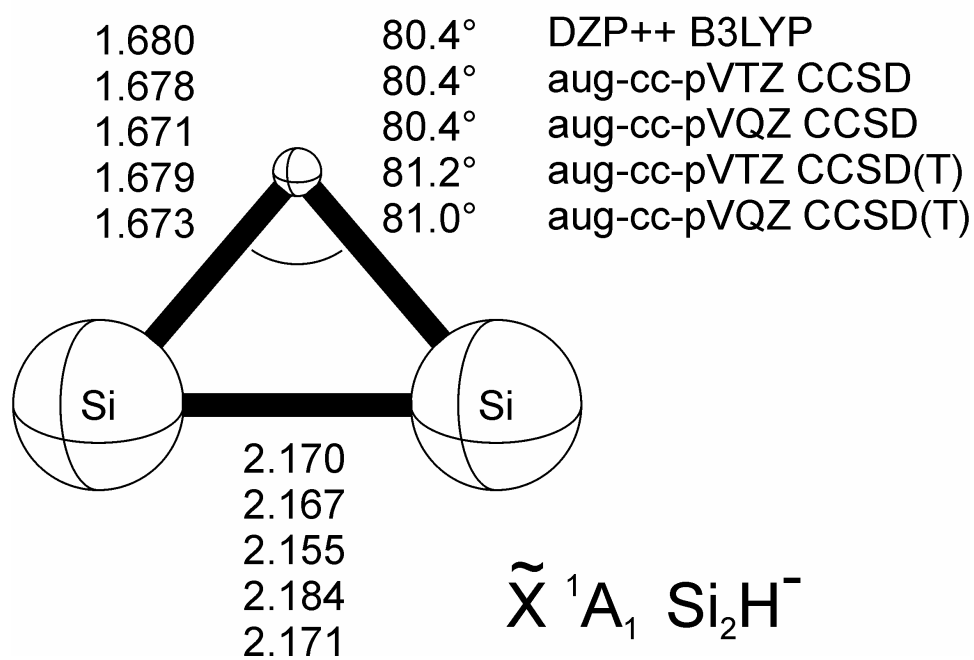
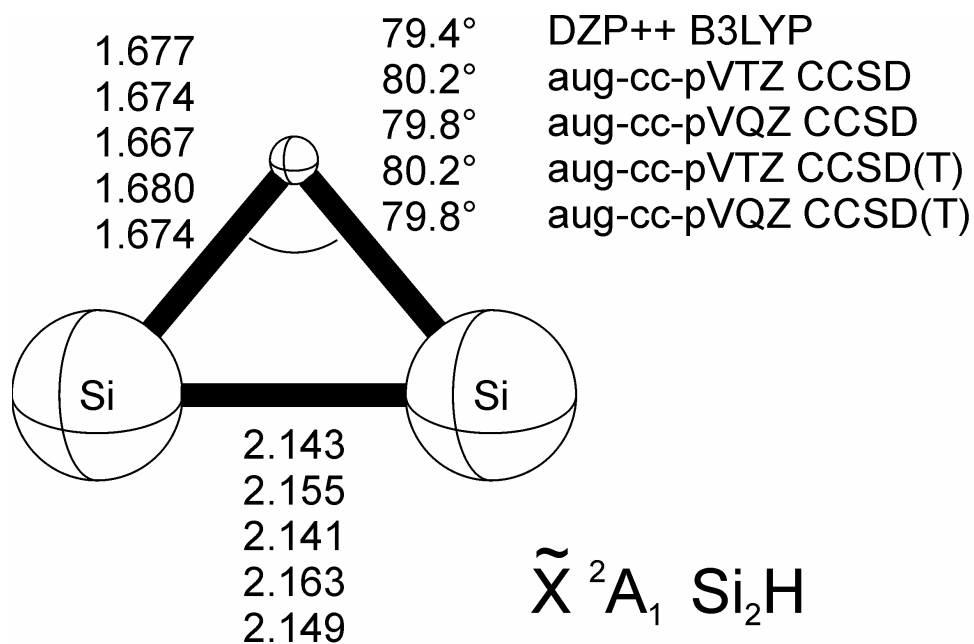


FIGURE 2. Geometrical parameters of the  $^2A_1 \text{ Si}_2\text{H}$  ground state and the  $^1A_1 \text{ Si}_2\text{H}^-$  anion ground state geometries.

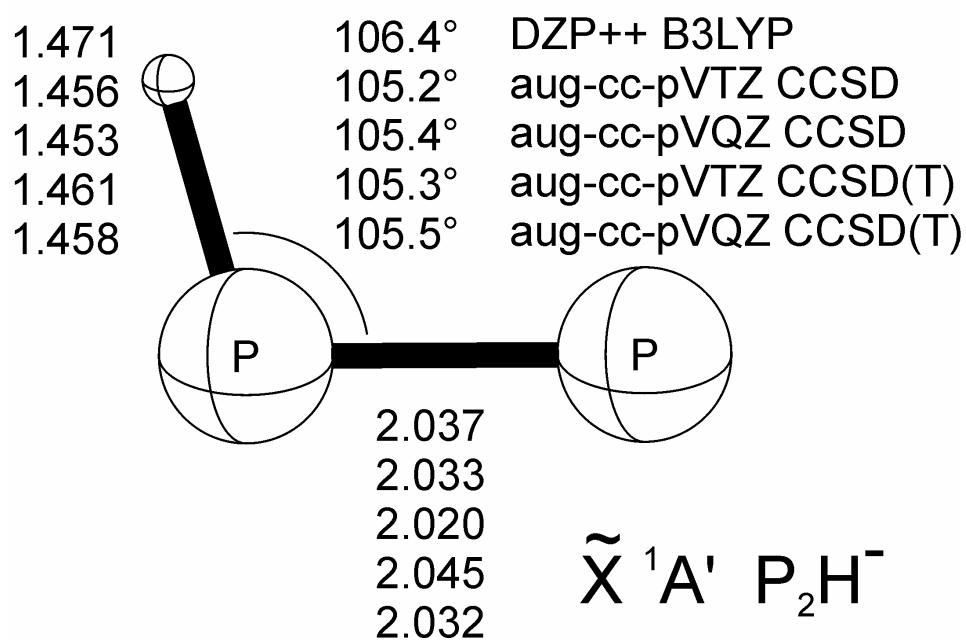
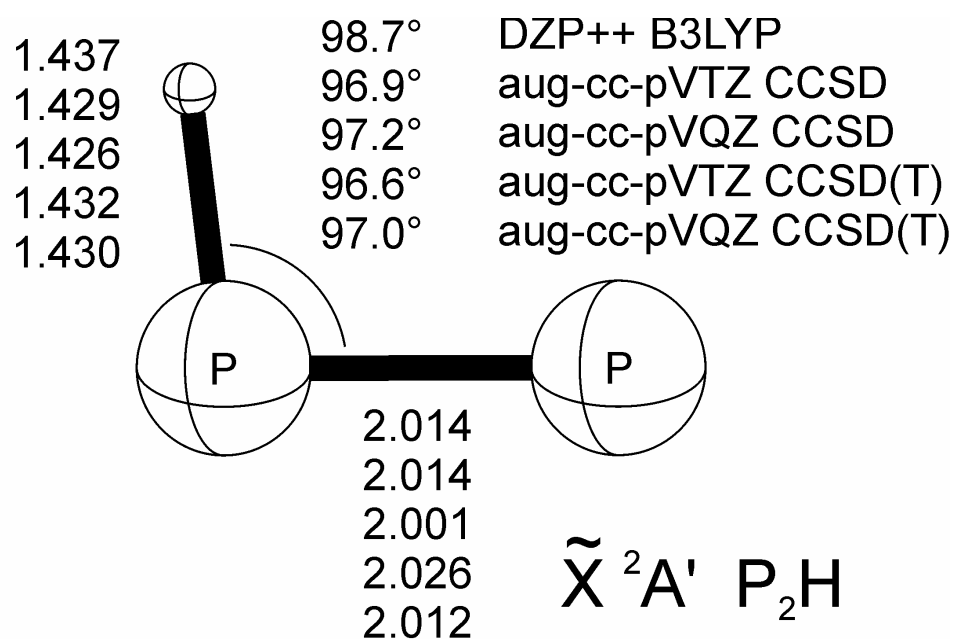


FIGURE 3. Geometrical parameters of the  $^2A'$   $P_2H$  ground state and the  $^1A'$   $P_2H^-$  anion ground state.

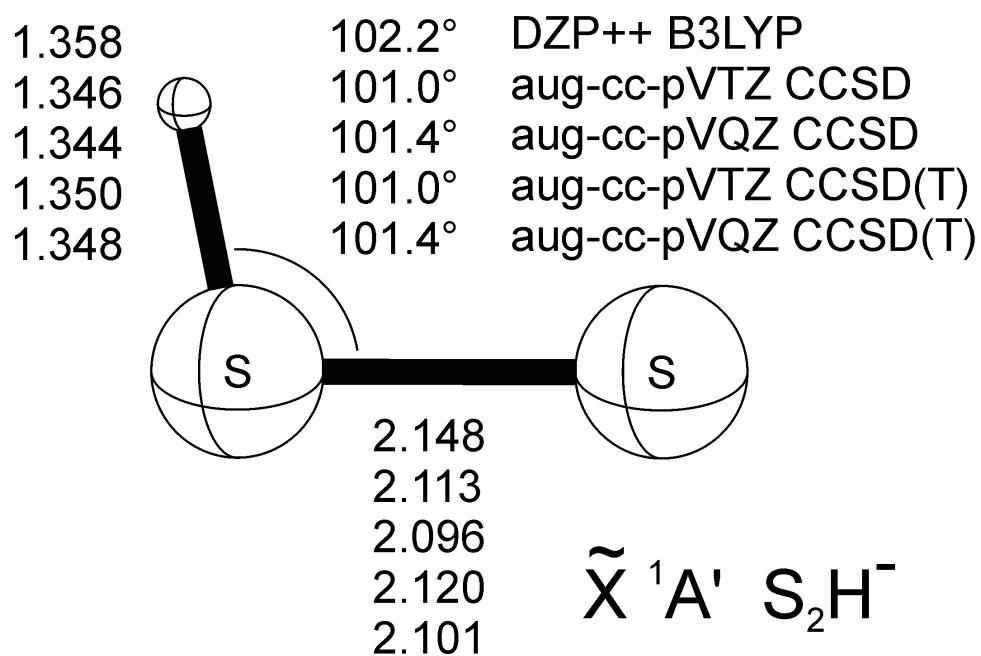
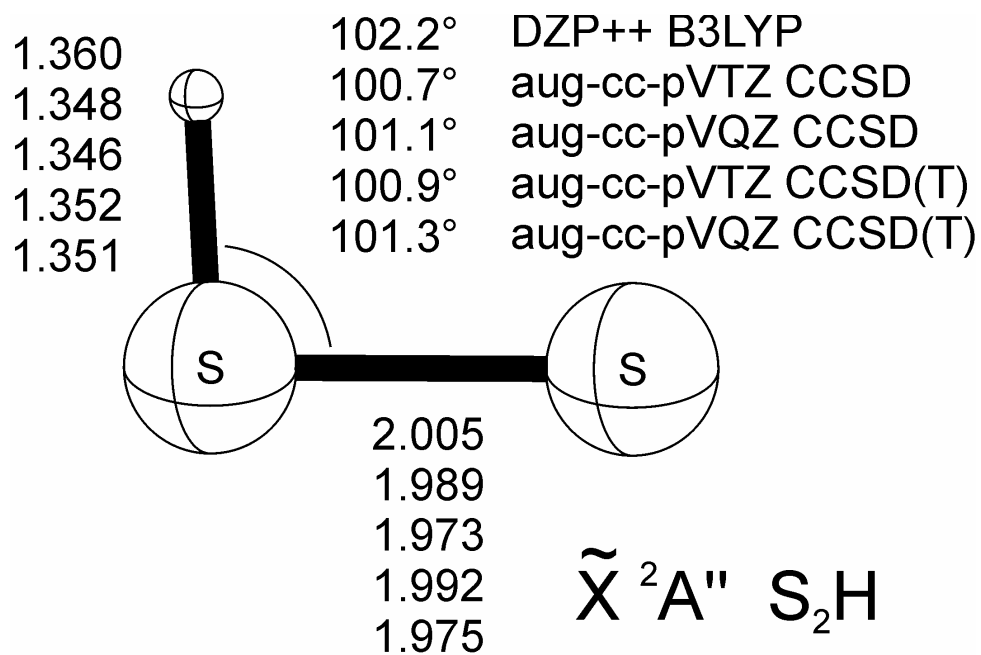


FIGURE 4. Geometrical parameters of the  $^2A'' S_2H$  ground state and the  $^1A' S_2H^-$  anion ground state.



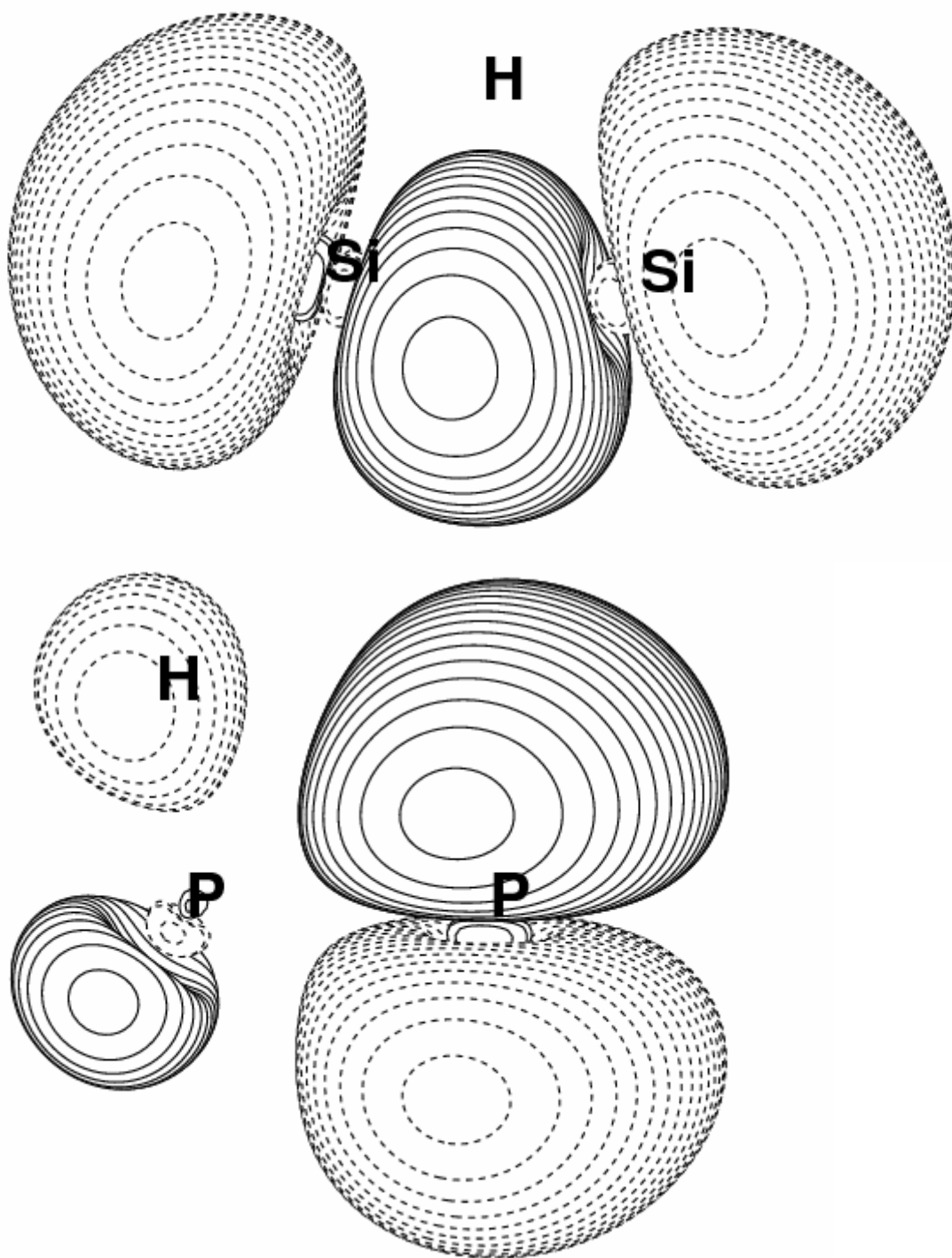


FIGURE 5.  $\text{Si}_2\text{H } ^2\text{A}_1$  HOMO and  $\text{P}_2\text{H } ^2\text{A}'$  HOMO.

## CHAPTER 3

### CONCLUDING REMARKS

*Ab initio* theory has once again provided useful insight into the properties of molecules which have not been studied extensively by experiment. Accurate theoretical properties are not only useful in themselves, but can help guide future experimental work on these and related systems.

From high level structural studies of the  $X_2H$  hydrides ( $X=Al$ ,  $Si$ ,  $P$ , and  $S$ ) it has been demonstrated that the  $Al_2H$  and  $Si_2H$  species have H-bridged structures of  $C_{2v}$  symmetry as their ground electronic states while the  $P_2H$  and  $S_2H$  isomers were found to have bent structures of  $C_s$  symmetry. This interesting change in ground state geometry may be attributed to a favorable overlap of the aluminum and silicon  $\pi_u$  bonding orbitals with the hydrogen  $1s$  orbital becoming unfavorable for the phosphorous and sulfur hydrides.

The B3LYP/DZP++ level of theory has again proven to be a rather robust method for computing electron affinities, comparing well to our most rigorous theoretical methods for these  $X_2H$  hydrides. In fact, B3LYP provided results for electron affinities nearly comparable in accuracy to the CCSD(T)/aug-cc-pVQZ method. The AEA at the CCSD(T)/aug-cc-pVQZ (B3LYP/DZP++) levels for  $Al_2H$  are predicted to be 1.11 eV (0.95 eV); for  $Si_2H$  the AEAs are 2.34 eV(2.31 eV); for  $P_2H$  the AEAs are 1.51 eV(1.53 eV); and for  $S_2H$  the AEAs are 1.93 eV(1.95 eV). With the exception of BP86 for  $Al_2H$ , the BLYP, BP86, and BHLYP functionals were not as successful as B3LYP in predicting adiabatic electron affinities.

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